

# Monolithic Amplifier

TSS-23HLN+

 $50\Omega$  30 MHz to 2 GHz

#### THE BIG DEAL

- High IP3, +42.6 dBm typ. at 1GHz
- Gain, 21.8 dB typ. at 1 GHz
- · Low noise figure, 1.4 dB at 1 GHz
- High P1dB, +28.5 dBm at 1 GHz
- Shutdown feature



Generic photo used for illustration purposes only

CASE STYLE: DQ1225

+RoHS Compliant
The +Suffix identifies RoHS Compliance.
See our website for methodologies and qualifications

#### **APPLICATIONS**

- Base station infrastructure
- CATV
- Cellular

#### **PRODUCT OVERVIEW**

TSS-23HLN+ (RoHS compliant) is an advanced wideband amplifier with shutdown feature. It is fabricated using E-PHEMT technology and offers extremely high dynamic range over a broad frequency range and with low noise figure. In addition, the TSS-23HLN+ has good input and output return loss over a broad frequency range. TSS-23HLN+ is enclosed in a 3mm x 3mm, 12-lead MCLP package and has very good thermal performance.

#### **KEY FEATURES**

Feature	Advantages
Broad Band: 30MHz to 2GHz	Broadband covering primary wireless communications bands: VHF, UHF, Cellular
Extremely High IP3 +39.6 dBm typical at 30 MHz +42.6 dBm typical at 1GHz	The TSS-23HLN+ matches industry leading IP3 performance relative to device size and power consumption. The combination of the design and E-PHEMT Structure provides enhanced linearity over a broad frequency range as evidence in the IP3 being approximately 13-15 dB above the P1dB point. This feature makes this amplifier ideal for use in:  • Driver amplifiers for complex waveform up converter paths • Drivers in linearized transmit systems • Secondary amplifiers in ultra-High Dynamic range receivers
Shutdown feature	Allow users to turn on and off the amplifier with pulsed signals while keeping the power supply at constant voltage to minimize DC power consumption
Low Noise Figure, 1.4 dB at 1 GHz	Enables lower system noise figure performance and along with High OIP3 provides high dynamic range
High P1dB , +28.5 dBm at 1 GHz	High P1dB, High OIP3, Low NF results in a very dynamic range preventing amplifier saturation under strong interfering signals.

REV. B ECO-022590 TSS-23HLN+ MCL NY 240731



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### TSS-23HLN+

#### ELECTRICAL SPECIFICATIONS¹ AT +25°C & 50Ω, UNLESS NOTED OTHERWISE

			Amplifier-ON		Amplifier-OFF	
Parameter	Condition (MHz)	VDD = +8V			VDD = +8V	Units
		Min. Typ. Max.			Тур.	
Frequency Range		30		2000	30-2000	MHz
	30		1.4		_	
	500		1.4		_	
Noise Figure	1000		1.4		_	dB
	1500		1.5		_	
	2000		1.6		_	
	30	20.9	23.3	25.5	-21	
	500	_	22.4	_	-21	
Gain	1000	19.5	21.8	23.8	-23	dB
	1500	_	21.1	_	-25	
	2000	18.1	20.3	22.1	-28	
Reversed Isolation	30-2000		27		26	dB
	30		11		12	
	500		12		12	
nput Return Loss	1000		10		12	dB
	1500		11		15	
	2000		12		20	
	30		15		2	
	500		14		2	
Output Return Loss	1000		12		2	dB
	1500		10		2	
	2000		8		2	
	30		+26.2			
	500		+27.9			
Output Power @1dB compression AMP-ON	1000		+28.5			dBm
	1500		+28.1			
	2000		+27.7			
	30	_	+39.6			
	500	_	+41.6			
Output IP3 (Pout = 0dBm/Tone)	1000	_	+42.6			dBm
	1500	+38.2	+42.6			
	2000	_	+41.8			
Device Operating Voltage (VDD)		+7.6	+8	+8.4	+8	V
Device Operating Current (ID)			236	249	8	mA
Control Voltage (VG)			0		+5	V
OC Current (ID) Variation Vs. Temperature <sup>2</sup>			-225			uA/degC
OC Current (ID) Variation Vs. Voltage			0.0263			mA/mV
hermal Resistance			23.3			degC/W

<sup>1.</sup> Measured on Mini-Circuits Characterization test board TB-TSS-23HLN+. See Characterization Test Circuit (Fig. 1)

#### **ABSOLUTE MAXIMUM RATINGS<sup>3</sup>**

Parameter	Ratings		
Operating Temperature (ground lead)	-40°C to 95°C		
Storage Temperature	-65°C to 150°C		
Total Power Dissipation	3.3 W		
Input Power	+28 dBm (5 minutes max.) +15 dBm (continuos) for 0.03-1 GHz +18 dBm (continuos) for 1-2 GHz		
DC Voltage V <sub>DD</sub> <sup>4</sup> (Pad 7)	+10 V		
DC Voltage V <sub>G</sub> <sup>5</sup> (Pad 1)	+10 V		

<sup>3</sup> Permanent damage may occur if these limits are exceeded.

#### **CONTROL VOLTAGE (V<sub>G</sub>) FIG. 1**

	Min.	Тур.	Max.	Units
Amplifier-ON	_	0	0.7	V
Amplifier-OFF	1.9	5	_	V

<sup>2. (</sup>Current at  $95^{\circ}$ C — Current at  $-45^{\circ}$ C)/140

<sup>4</sup> Measured by keeping VG=0V.

<sup>5</sup> Measured by keeping Vdd=8V.

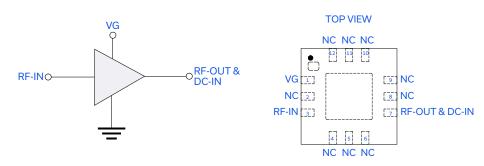


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#### **SWITCHING SPECIFICATIONS**

Parameter	Min.	Тур.	Max.	Units	
Amplifier ON to Chutdour	OFF TIME (50% Control to 10% RF)	_	5.3	_	μs
Amplifier ON to Shutdown	FALL TIME (90 to 10% RF)	_	7.3	_	
Association Chartelesson to ON	ON TIME (50% Control to 90% RF)	_	77.7	_	
Amplifier Shutdown to ON	RISE TIME (10% to 90% RF)	_	54.2	_	μs
Control Voltage Leakage		_	633.3	_	mV

#### SIMPLIFIED SCHEMATIC AND PAD DESCRIPTION

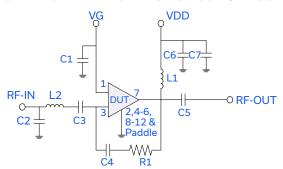


Function	Pad Number	Description
RF-IN	3	RF Input
RF-OUT and DC-IN	7	RF Output and DC Bias
GND	Paddle	Connections to ground.
NC	2, 4-6, 8-12	No connection, grounded externally
VG	1	Control voltage for shutdown (VG)



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#### CHARACTERIZATION TEST CIRCUIT / RECOMMENDED APPLICATION CIRCUIT



Component	Size	Value	Part Number	Manufacturer
C1	0402	0.1uF	GRM155R71C104KA88D	Murata
C2	0402	1.2pF	GRM1555C1H1R2CA1D	Murata
C3	0402	0.1uF	GRM155R71C104KA88D	Murata
C4	0402	0.1uF	GRM155R71C104KA88D	Murata
C5	0402	1000pF	GRM1555C1H102JA01D	Murata
C6	0402	10000pF	GRM155R71E103KA01D	Murata
C7	0402	0.1uF	GRM155R71C104KA88D	Murata
L1	0805	680nH	0805LS-681XJLB	Coilcraft
L2	0402	1.0nH	0402CS-1N0XJLW	Coilcraft
R1	0402	1.2K0hm	RK73H1ETTP1201F	Koa

Fig 1. Block diagram of Test Circuit used for characterization. (DUT soldered on Mini-Circuits Characterization test board TB-TSS-13LN+) Gain, Return loss, Output power at 1dB compression (P1dB), output IP3 (OIP3) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

#### Conditions:

- 1. Gain and Return Loss:  $P_{\scriptscriptstyle \rm IN}$ = -25 dBm
- 2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, +0dBm/tone at output.
- 3. Switching Time

RF Signal:  $P_{\rm IN}$ =-25 dBm, fRF=500 MHz. Vdd=+8V DC, VG=Pulse signal at 1 KHz with VHIGH=+5V, VLOW=0V, 50% duty cycle.

#### **PRODUCT MARKING**



Marking may contain other features or characters for internal lot control



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#### ADDITIONAL DETAILED TECHNICAL INFORMATION IS AVAILABLE ON OUR DASHBOARD.

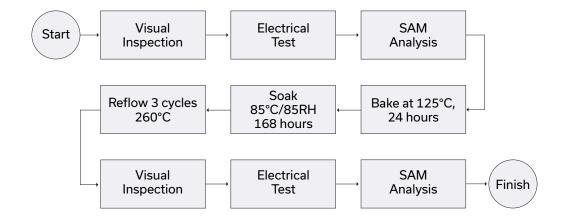
**CLICK HERE** 

Performance Data	Data Table Swept Graphs S-Parameter (S2P Files) Data Set (.zip file)	
Case Style	DQ1225 Plastic package, exposed paddle lead finish: Matte-Tin	
Tape & Reel Standard quantities available on reel	F66 7" reels with 20, 50, 100, 200, 500, 1K, or 2K devices	
Suggested Layout for PCB Design	PL-619	
Evaluation Board	TB-TSS-23HLN+	
Environmental Ratings	ENV08T9	

#### **ESD RATING**

Human Body Model (HBM): Class 1A (Pass 250 V) in accordance with ANSI/ESD STM 5.1 - 2001

#### **MSL FLOW CHART**



#### NOTES

- A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.
- B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.
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